

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of: Jae Han CHA

Serial No.: New Application Group Art Unit: Not Yet Assigned

Filed: July 3, 2003 Examiner: Not Yet Assigned

Title: METHOD OF FORMING AN ISOLATION FILM IN A SEMICONDUCTOR DEVICE

INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

July 3, 2003

Sir:

As a means of complying with the duty of disclosure under 37 CFR §1.56, and in accordance with 37 CFR §§1.97 and 1.98, Applicant(s), through the undersigned attorney, submits this Information Disclosure Statement. The patents, publications or other information submitted herewith are listed on the attached Form PTO-1449 and copies are attached.

In accordance with 37 CFR §1.97(b)(1) or (2), this Information Disclosure Statement is being filed either within three months of the filing date of the above-identified application, or within three months of the date of entry into the national stage of the above-identified application as set forth in 37 CFR §1.491. Accordingly, no fee is required.

Respectfully submitted,

JACOBSON HOLMAN, PLLC

By:


Yoon S. Ham

Registration No. 45,307

400 Seventh Street, N.W.
Washington, DC 20004
(202) 638-6666

Atty. Dkt. No.: P68962US0
YSH: dj

JACOBSON HOLMAN, PLLC
400 SEVENTH STREET, N.W.
WASHINGTON, D.C. 20004-2201

LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

ATTY. DOCKET NO.: P68962US0 GROUP ART UNIT: Not Yet Assigned
SERIAL NO.: New Application FILING DATE: July 3, 2003
APPLICANT(S): Jae Han CHA TODAY'S DATE: July 3, 2003

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	INT'L CLASS	SUB- CLASS	FILING DATE (If Appropriate)
AA	_____	_____	_____	_____	_____	_____
AB	_____	_____	_____	_____	_____	_____

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION (YES) (NO)
AC	_____	_____	_____	_____	_____
AD	_____	_____	_____	_____	_____
AE	_____	_____	_____	_____	_____

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

AF S. J. Ahn, et al.; "Novel DRAM Cell Transistor with Asymmetric Source and Drain Junction Profiles Improving Data Retention Characteristics"; 2002 Symposium On VLSI Technology Digest of Technical Papers; pp. 176-177.

EXAMINER _____ DATE CONSIDERED _____

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).